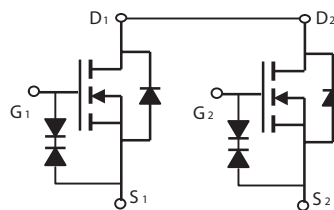
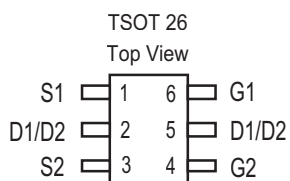


**Dual N-Channel Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
20V	5.5A	24.5 @ V _{GS} =4.5V
		25.5 @ V _{GS} =4.0V
		27.5 @ V _{GS} =3.7V
		30.5 @ V _{GS} =3.1V
		36.5 @ V _{GS} =2.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.

**ABSOLUTE MAXIMUM RATINGS** (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous ^a	T _A =25°C	5.5
		T _A =70°C	4.4
I _{DM}	-Pulsed ^b	22	A
P _D	Maximum Power Dissipation ^a	T _A =25°C	1.25
		T _A =70°C	0.8
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	100	°C/W
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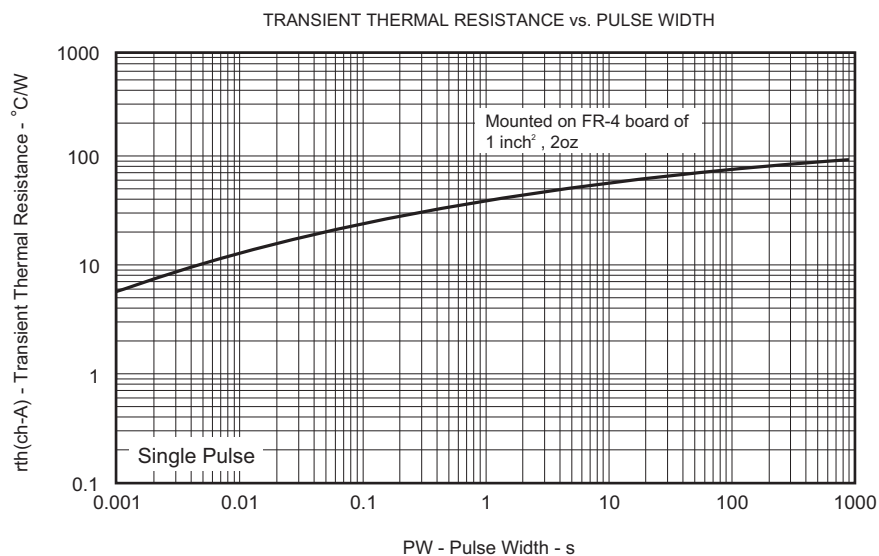
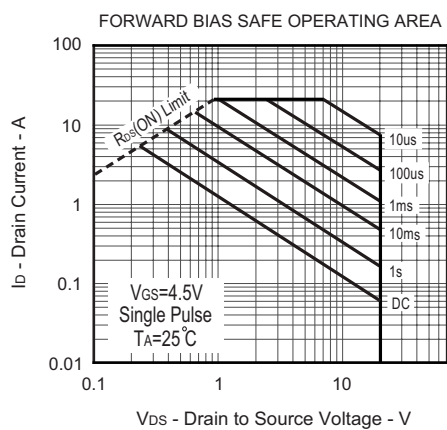
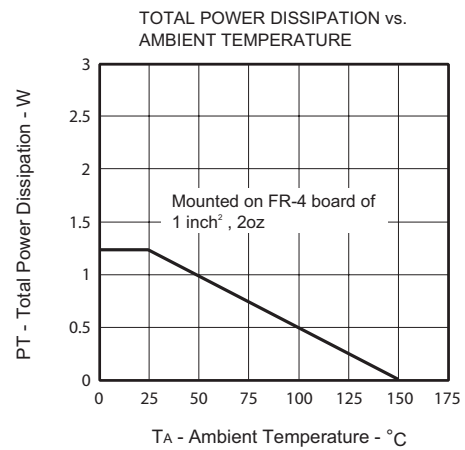
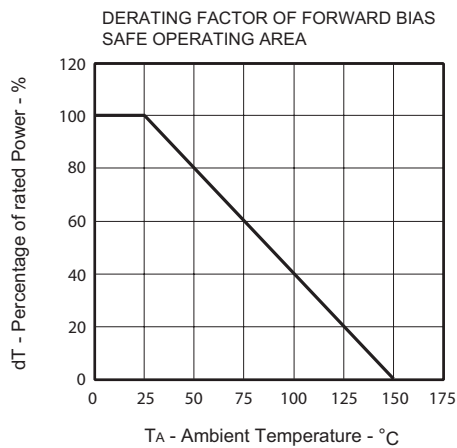
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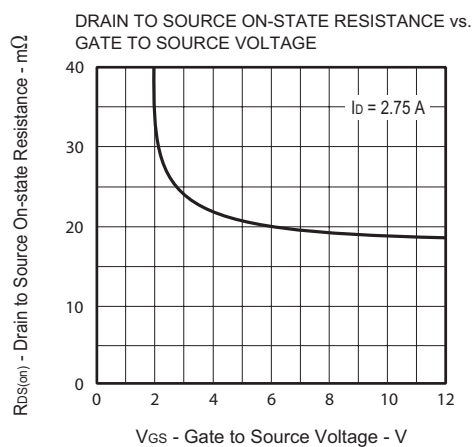
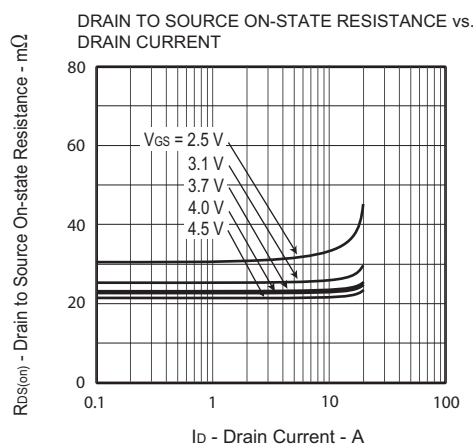
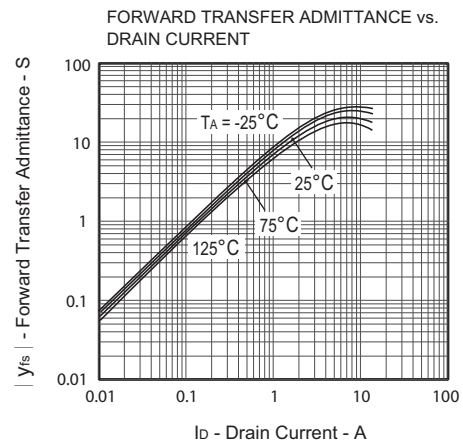
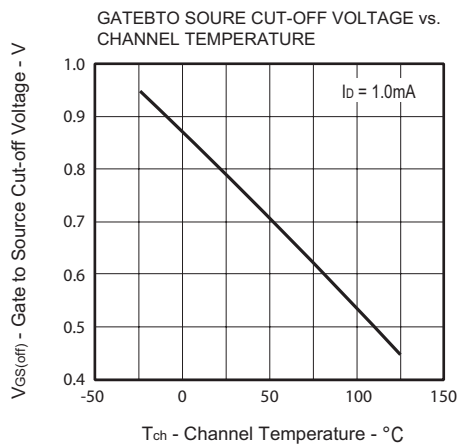
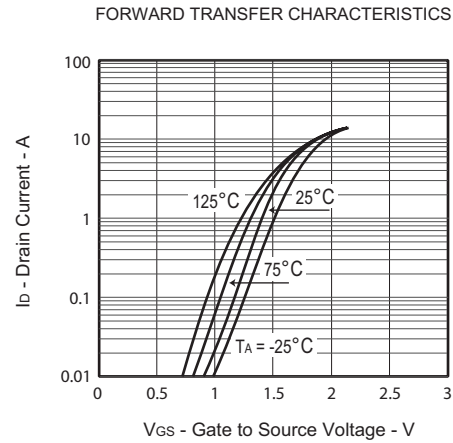
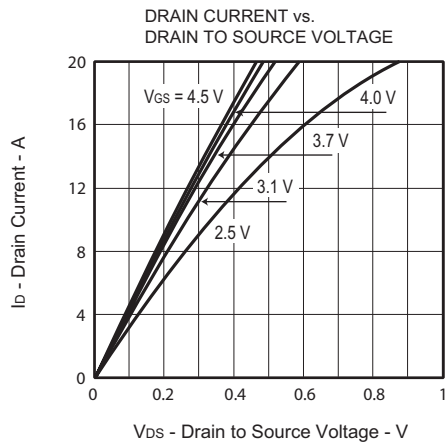
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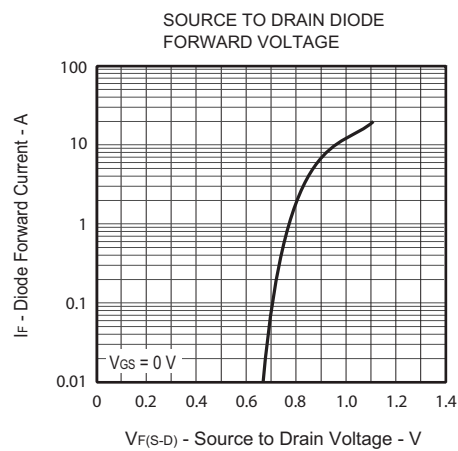
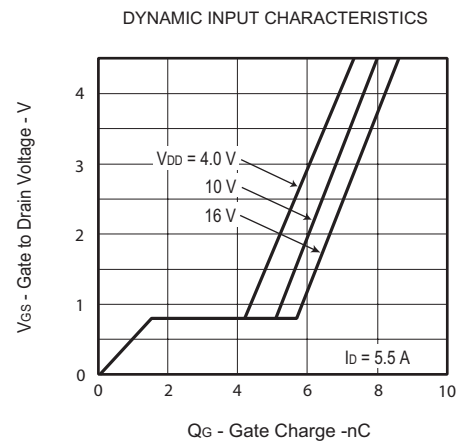
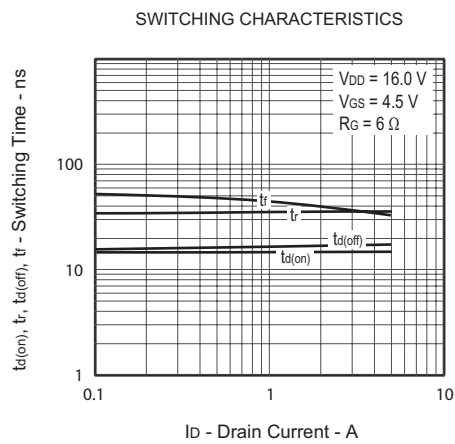
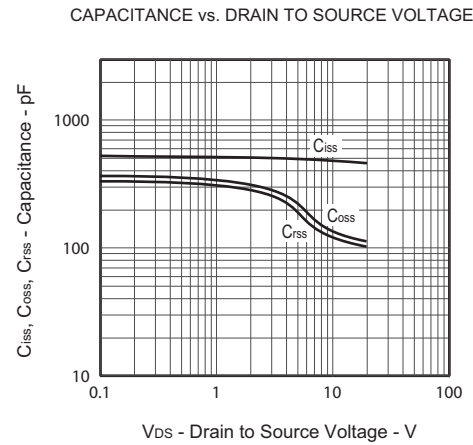
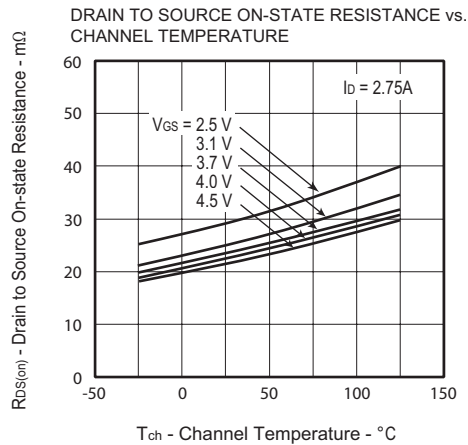
ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±12V , V _{DS} =0V			±10	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =1mA	0.5	0.9	1.5	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =4.5V , I _D =2.75A	18.5	21.5	24.5	m ohm
		V _{GS} =4.0V , I _D =2.75A	19.5	22.5	25.5	m ohm
		V _{GS} =3.7V , I _D =2.75A	20.5	23.5	27.5	m ohm
		V _{GS} =3.1V , I _D =2.75A	21.5	25.5	30.5	m ohm
		V _{GS} =2.5V , I _D =2.75A	23.5	29.5	36.5	m ohm
g _{FS}	Forward Transconductance	V _{DS} =5V , I _D =2.75A		15		S
DYNAMIC CHARACTERISTICS °						
C _{iss}	Input Capacitance	V _{DS} =10V,V _{GS} =0V f=1.0MHz		485		pF
C _{oss}	Output Capacitance			155		pF
C _{RSS}	Reverse Transfer Capacitance			135		pF
SWITCHING CHARACTERISTICS °						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =16V I _D =2.75A V _{GS} =4.5V R _{GEN} = 6 ohm		16.5		ns
t _r	Rise Time			36		ns
t _{D(OFF)}	Turn-Off Delay Time			18		ns
t _f	Fall Time			39		ns
Q _g	Total Gate Charge	V _{DS} =16V,I _D =5.5A, V _{GS} =4.5V		8.6		nC
Q _{gs}	Gate-Source Charge			1.5		nC
Q _{gd}	Gate-Drain Charge			4.2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V,I _S =1A		0.78	1.2	V
Notes						
a.Surface Mounted on FR4 Board,t ≤ 10sec.						
b.Pulse Test:Pulse Width ≤ 10us, Duty Cycle ≤ 1%.						
c.Guaranteed by design, not subject to production testing.						

Aug,04,2011

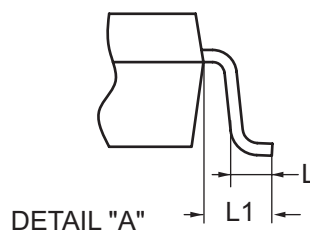
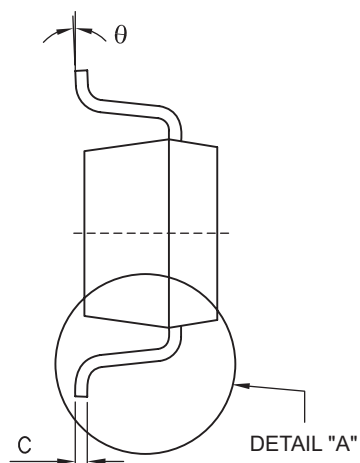
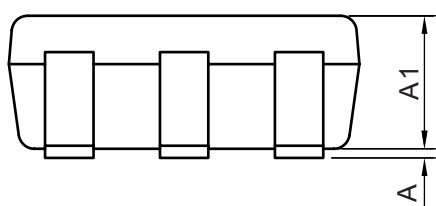
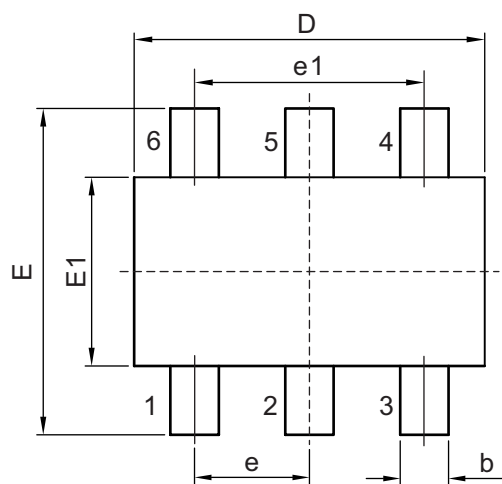






PACKAGE OUTLINE DIMENSIONS

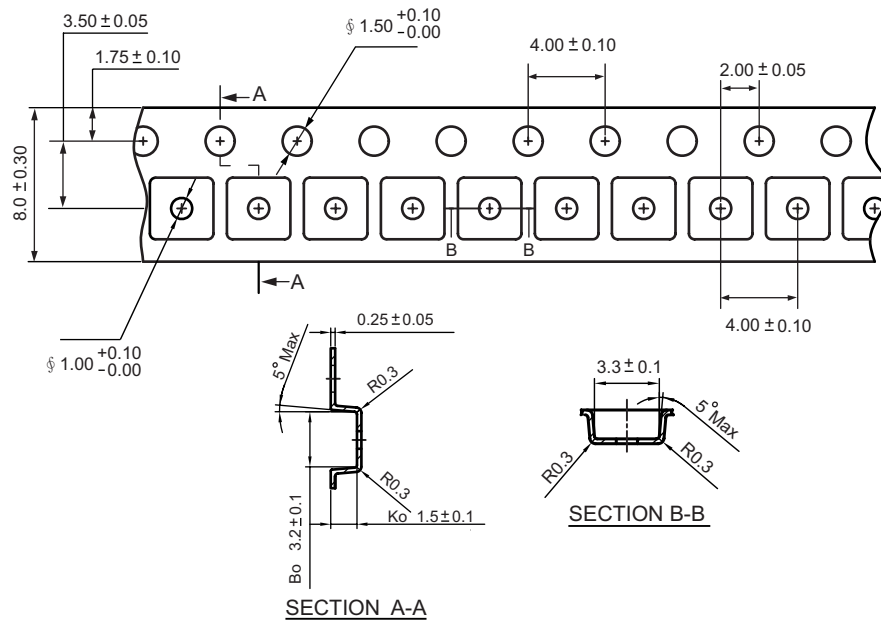
TSOT 26



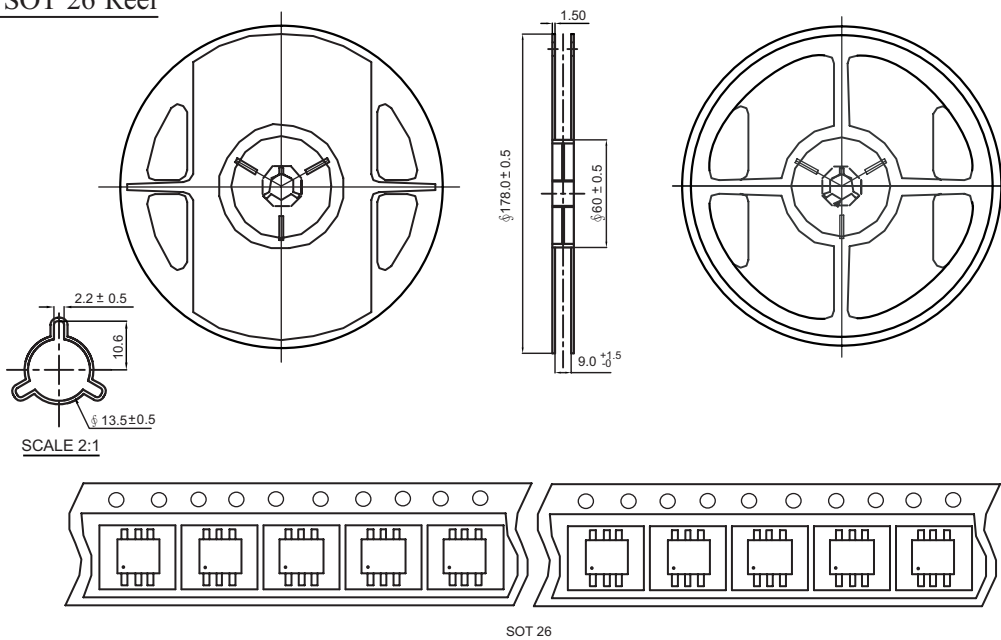
SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
D	2.692	3.099	0.106	0.122
E	2.591	3.000	0.102	0.118
E1	1.397	1.803	0.055	0.071
e	0.950 REF.		0.037 REF.	
e1	1.900 REF.		0.075 REF.	
b	0.300	0.500	0.012	0.020
C	0.080	0.200	0.003	0.008
A	0.000	0.100	0.000	0.004
A1	0.700	0.800	0.028	0.032
L	0.300	0.600	0.012	0.024
L1	0.600 REF.		0.023 REF.	
θ	0°	6°	0°	6°

TSOT 26 Tape and Reel Data

TSOT 26 Carrier Tape



TSOT 26 Reel



SOT 26